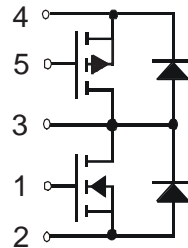


Polar™ P & N-Channel Power MOSFET Common Drain Topology

FMP26-02P

(Electrically Isolated Tab)



| | P CH. | N CH. |
|---------------|--------|-------|
| V_{DSS} | - 200V | 200V |
| I_{D25} | - 17A | 26A |
| $R_{DS(on)}$ | 170mΩ | 60mΩ |
| $t_{rr(typ)}$ | 240ns | 150ns |

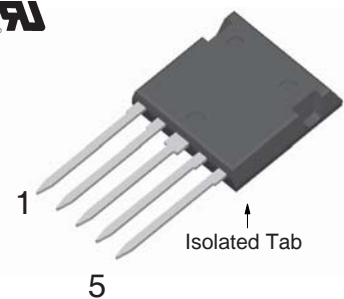
| Symbol | Test Conditions | Maximum Ratings | |
|-------------|--------------------------------------|-------------------|-------|
| T_J | | -55 ... +150 | °C |
| T_{JM} | | 150 | °C |
| T_{stg} | | -55 ... +150 | °C |
| V_{ISOLD} | 50/60Hz, RMS, t = 1min, Leads-to-Tab | 2500 | ~V |
| T_L | 1.6mm (0.062 in.) from Case for 10s | 300 | °C |
| T_{SOLD} | Plastic Body for 10s | 260 | °C |
| F_C | Mounting Force | 20..120 / 4.5..27 | N/lb. |

| Symbol | Test Conditions | Characteristic Values | | |
|---------------|--|-----------------------|------|------|
| | | Min. | Typ. | Max. |
| C_P | Coupling Capacitance Between Shorted Pins and Mounting Tab in the Case | | 40 | pF |
| d_S, d_A | Pin - Pin | 1.7 | | mm |
| d_S, d_A | Pin - Backside Metal | 5.5 | | mm |
| Weight | | | 9 | g |

P - CHANNEL

| Symbol | Test Conditions | Maximum Ratings | |
|-----------|--|-----------------|---|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | - 200 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$ | - 200 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | -17 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM} | - 70 | A |
| I_A | $T_C = 25^\circ\text{C}$ | - 26 | A |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 1.5 | J |
| P_D | $T_C = 25^\circ\text{C}$ | 125 | W |

ISOPLUS i4-Pak™



Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
 - UL Recognized Package
 - Isolated Mounting Surface
 - 2500V~ Electrical Isolation
- Avalanche Rated
- Low Q_g
- Low Drain-to-Tab Capacitance
- Low Package Inductance

Advantages

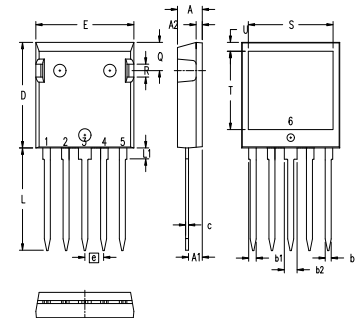
- Low Gate Drive Requirement
- High Power Density
- Low Drain to Ground Capacitance
- Fast Switching

Applications

- DC and AC Motor Drives
- Class AB Audio Amplifiers
- Multi-Phase DC to DC Converters
- Industrial Battery Chargers
- Switching Power Supplies

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|---|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V, I_D = -250\mu\text{A}$ | -200 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\mu\text{A}$ | -2.5 | | V |
| I_{GSS} | $V_{GS} = \pm 20V, V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$ | | | -10 μA -150 μA |
| $R_{DS(on)}$ | $V_{GS} = -10V, I_D = -13A$, Note 1 | | | 170 m Ω |
| g_{fs} | $V_{DS} = -10V, I_D = -13A$, Note 1 | 10 | 17 | S |
| C_{iss} | $V_{GS} = 0V, V_{DS} = -25V, f = 1\text{MHz}$ | | 2740 | pF |
| C_{oss} | | | | |
| C_{rss} | | | | |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = -10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = -13A$ $R_G = 3.3\Omega$ (External) | | 18 | ns |
| t_r | | | | |
| $t_{d(off)}$ | | | | |
| t_f | | | | |
| $Q_{g(on)}$ | $V_{GS} = -10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = -13A$ | | 56 | nC |
| Q_{gs} | | | | |
| Q_{gd} | | | | |
| R_{thJC} | | | | 1.0 $^\circ\text{C/W}$ |
| R_{thCS} | | 0.15 | | $^\circ\text{C/W}$ |

ISOPLUS i4-Pak™ Outline



NOTE: Bottom heatsink meets 3000 Volts AC 1 sec isolation to the other pins.

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .190 | .205 | 4.83 | 5.21 |
| A1 | .102 | .118 | 2.59 | 3.00 |
| A2 | .046 | .085 | 1.17 | 2.16 |
| b | .045 | .055 | 1.14 | 1.40 |
| b1 | .058 | .068 | 1.47 | 1.73 |
| b2 | .100 | .110 | 2.54 | 2.79 |
| C | .020 | .029 | 0.51 | 0.74 |
| D | .819 | .840 | 20.80 | 21.34 |
| E | .770 | .799 | 19.56 | 20.29 |
| e | .150 BSC | | 3.81 BSC | |
| L | .780 | .840 | 19.81 | 21.34 |
| L1 | .083 | .102 | 2.11 | 2.59 |
| Q | .210 | .244 | 5.33 | 6.20 |
| R | .100 | .180 | 2.54 | 4.57 |
| S | .660 | .690 | 16.76 | 17.53 |
| T | .590 | .620 | 14.99 | 15.75 |
| U | .065 | .080 | 1.65 | 2.03 |

Ref: IXYS CO 0077 R0

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|------|--------|
| | | Min. | Typ. | Max. |
| I_s | $V_{GS} = 0V$ | | | -17 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | -104 A |
| V_{SD} | $I_F = -13A, V_{GS} = 0V$, Note 1 | | | -3.2 V |
| t_{rr} | $I_F = -13A, di/dt = 100A/\mu\text{s}$ $V_R = -100V, V_{GS} = 0V$ | | 240 | ns |
| Q_{RM} | | | | |
| I_{RM} | | | | |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

N - CHANNEL

| Symbol | Test Conditions | Maximum Ratings | |
|-----------|--|-----------------|---|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 200 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$ | 200 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 26 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM} | 120 | A |
| I_A | $T_C = 25^\circ\text{C}$ | 50 | A |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 1 | J |
| P_D | $T_C = 25^\circ\text{C}$ | 125 | W |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|--|-----------------------|------|---------------------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$ | 200 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$ | 2.5 | | 5.0 V |
| I_{GSS} | $V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0\text{V}$ $T_J = 150^\circ\text{C}$ | | | 25 μA 250 μA |
| $R_{DS(on)}$ | $V_{GS} = 10\text{V}$, $I_D = 25\text{A}$, (Note 1) | | | 60 m Ω |
| g_{fs} | $V_{DS} = 10\text{V}$, $I_D = 25\text{A}$, (Note 1) | 12 | 23 | S |
| C_{iss} | } $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 2720 | pF |
| C_{oss} | | | 490 | pF |
| C_{rss} | | | 105 | pF |
| $t_{d(on)}$ | } Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 25\text{A}$ $R_G = 10\Omega$ (External) | | 26 | ns |
| t_r | | | 35 | ns |
| $t_{d(off)}$ | | | 70 | ns |
| t_f | | | 30 | ns |
| $Q_{g(on)}$ | } $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 25\text{A}$ | | 70 | nC |
| Q_{gs} | | | 17 | nC |
| Q_{gd} | | | 37 | nC |
| R_{thJC} | | | | 1.0 $^\circ\text{C/W}$ |
| R_{thCS} | | 0.15 | | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|------|---------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0V$ | | | 26 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 120 A |
| V_{SD} | $I_F = 50A, V_{GS} = 0V$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 25A, -di/dt = 100A/\mu s$ $V_R = 100V, V_{GS} = 0V$ | | 150 | ns |
| Q_{RM} | | | 2.0 | μC |

Note 1: Pulse test, $t \leq 300\mu s$, duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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